



PROGRAMMABLE OVERVOLTAGE PROTECTOR QUAD FORWARD-CONDUCTING P-GATE THYRISTOR

TISP61089QB SLIC Overvoltage Protector

Quad Voltage-Programmable Protector

- Wide -20 V to -155 V Programming Range
- Low 5 mA max. Gate Triggering Current
- High 150 mA min. Holding Current
- Rated for ITU-T and YD/T-950 10/700 impulses
- Rated for Telcordia Intra-building impulses

10/700 Protection Voltage Specified

Element	Protection Level 40 A, 5/310
Diode	+12
Crowbar $V_{GG} = -48\text{ V}$	-64

Description

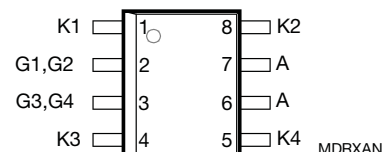
Bourns® TISP61089QB is a quad forward-conducting buffered p-gate overvoltage protector. It is designed to protect monolithic SLICs (Subscriber Line Interface Circuits) against overvoltages on the telephone line caused by lightning, a.c. power contact and induction. The TISP61089QB limits voltages that exceed the SLIC supply rail voltage. The TISP61089QB parameters are specified to allow equipment compliance with Telcordia GR-1089-CORE Intra-building, ITU-T K.20, K.21 and K.45 and YD/T-950.

The SLIC line driver section is typically powered from 0 V (ground) and a negative voltage in the region of -20 V to -155 V. The protector gate is connected to this negative supply. This references the protection (clipping) voltage to the negative supply voltage. As the protection voltage will then track the negative supply voltage the overvoltage stress on the SLIC is minimized.

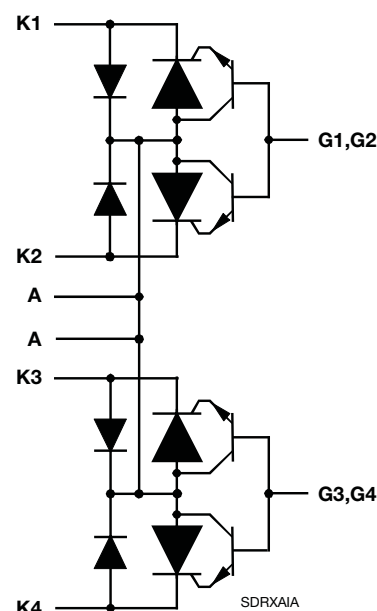
Positive overvoltages are clipped to ground by diode forward conduction. Negative overvoltages are initially clipped close to the SLIC negative supply rail value. If sufficient current is available from the overvoltage, then the protector will crowbar into a low voltage on-state condition. As the overvoltage subsides, the high holding current of the crowbar helps prevent d.c. latchup.

These monolithic protection devices are fabricated in ion-implanted planar vertical power structures for high reliability and are virtually transparent in normal operation. The TISP61089QB buffered gate design reduces the loading on the SLIC supply during overvoltages caused by power cross and induction. The TISP61089QB is available in an 8-pin plastic small-outline surface mount package.

D Package (Top View)



Device Symbol



How to Order

Device	Package	Carrier	Order As	Marking Code	Standard Quantity
TISP61089QB	8 Pin Small Outline (D008)	Embossed Tape Reeled	TISP61089QBDR-S	1089QB	2500

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Absolute Maximum Ratings, $T_J = 25\text{ °C}$ (Unless Otherwise Noted)

Rating	Symbol	Value	Unit
Repetitive peak off-state voltage, $I_G = 0$	V_{DRM}	-170	V
Repetitive peak gate-cathode voltage, $V_{KA} = 0$	V_{GKRM}	-167	V
Non-repetitive peak on-state pulse current (see Notes 1 and 2) 10/1000 μ s (Bellcore GR-1089-CORE, Issue 1, November 1994, Section 4) 5/310 μ s (ITU-T K.20/21/45, YD/T-950, open circuit voltage waveshape 10/700) 2/40 μ s (IEC61000-4-5, 1.2/50 μ s open circuit voltage, 2 ohm + 10 ohm, see Note 4) 2/10 μ s (Bellcore GR-1089-CORE, Issue 1, November 1994, Section 4)	I_{TSP}	30 40 85 120	A
Non-repetitive peak on-state current, 60 Hz (see Notes 1, 2 and 3) 900 s	I_{TSM}	0.5	A
Non-repetitive peak gate current, 2/10 μ s pulse, cathodes commoned (see Notes 1 and 2)	I_{GSM}	40	A
Junction temperature	T_J	-40 to +150	°C
Storage temperature range	T_{stg}	-40 to +150	°C

- NOTES: 1. Initially the protector must be in thermal equilibrium with $T_J = 25\text{ °C}$. The surge may be repeated after the device returns to its initial conditions.
2. These non-repetitive rated currents are peak values for either polarity. The rated current values may be applied to any cathode-anode terminal pair. Additionally, all cathode-anode terminal pairs may have their rated current values applied simultaneously (in this case the anode terminal current will be four times the rated current value of an individual terminal pair).
3. EIA/JESD51-2 environment and EIA/JESD51-7 high effective thermal conductivity test board (multi-layer) connected with 0.6 mm printed wiring track widths.
4. Combination wave generator as specified in ITU-T K.20, K.21, K.44.

Recommended Operating Conditions

	Min	Typ	Max	Unit
C_G Gate decoupling capacitor		100		nF

Electrical Characteristics, $T_J = 25\text{ °C}$ (Unless Otherwise Noted)

Parameter	Test Conditions	Min	Typ	Max	Unit
I_D Off-state current	$V_D = V_{DRM}$, $V_{GK} = 0$			-5	μ A
$V_{(BO)}$ Breakover voltage	10/700 μ s, $I_T = -40$ A, $R_S = 55\ \Omega$, $V_{GG} = -48$ V, $C_G = 100$ nF			-64	V
V_F Forward voltage	$I_F = 5$ A, $t_w = 200\ \mu$ s			3	V
V_{FRM} Peak forward recovery voltage	10/700 μ s, $I_F = 40$ A, $R_S = 55\ \Omega$, $V_{GG} = -48$ V, $C_G = 100$ nF		12		V
I_H Holding current	$I_T = -1$ A, $di/dt = 1$ A/ms, $V_{GG} = -100$ V	-150			mA
I_{GAS} Gate reverse current	$V_{GG} = V_{GK} = V_{GKRM}$, $V_{KA} = 0$			-5	μ A
I_{GT} Gate trigger current	$I_T = 3$ A, $t_{p(g)} \geq 20\ \mu$ s, $V_{GG} = -100$ V			5	mA
V_{GT} Gate trigger voltage	$I_T = 3$ A, $t_{p(g)} \geq 20\ \mu$ s, $V_{GG} = -100$ V			2.5	V
C_{AK} Anode-cathode off-state capacitance	$f = 1$ MHz, $V_d = 1$ V $I_G = 0$, (see Note 5)	$V_D = -3$ V		100	pF
		$V_D = -48$ V		50	

- NOTE: 5. These capacitance measurements employ a three terminal capacitance bridge incorporating a guard circuit. The unmeasured device terminals are a.c. connected to the guard terminal of the bridge.

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Specifications are subject to change without notice.
Customers should verify actual device performance in their specific applications.

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Thermal Characteristics

Parameter	Test Conditions	Min	Typ	Max	Unit
$R_{\theta JA}$	Junction to free air thermal resistance			160	°C/W

Parameter Measurement Information

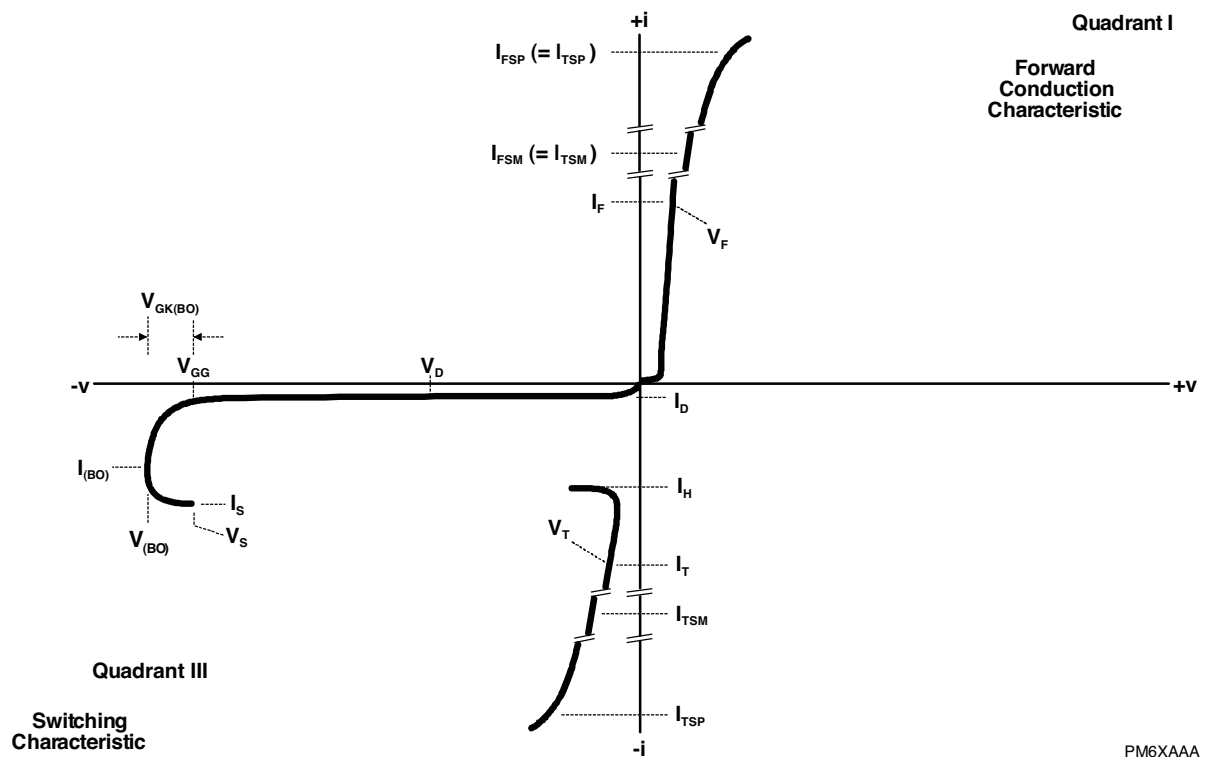


Figure 1. Voltage-Current Characteristic

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Typical Applications Circuit

Bourns Sales Offices

Region	Phone	Fax
The Americas:	+1-951-781-5500	+1-951-781-5700
Europe:	+41(0)41-7685555	+41(0)41-7685510
Asia-Pacific:	+886-2-25624117	+886-2-25624116

Technical Assistance

Region	Phone	Fax
The Americas:	+1-951-781-5500	+1-951-781-5700
Europe:	+41(0)41-7685555	+41(0)41-7685510
Asia-Pacific:	+886-2-25624117	+886-2-25624116

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9